#### 捷多邦,专业PCB打**SN154LV4小5**元急**SN74LVTH573** 3.3-V ABT OCTAL TRANSPARENT D-TYPE LATCHES WITH 3-STATE OUTPUTS

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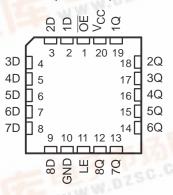
- State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static-Power Dissipation
- **Support Mixed-Mode Signal Operation** (5-V Input and Output Voltages With 3.3-V V<sub>CC</sub>)
- **Support Unregulated Battery Operation** Down to 2.7 V
- Typical V<sub>OLP</sub> (Output Ground Bounce)  $< 0.8 \text{ V at } V_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Ioff and Power-Up 3-State Support Hot
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Latch-Up Performance Exceeds 500 mA Per **JESD 17**
- **ESD Protection Exceeds 2000 V Per** MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Package, and Ceramic (J) **DIPs**

RODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments tandard warranty. Production processing does not necessarily include lesting of all parameters.

SN54LVTH573...JORWPACKAGE SN74LVTH573...DB, DW, OR PW PACKAGE (TOP VIEW)



SN54LVTH573 . . . FK PACKAGE (TOP VIEW)



#### description

These octal latches are designed specifically for low-voltage (3.3-V) V<sub>CC</sub> operation, but with the capability to provide a TTL interface to a 5-V system environment.

The eight latches of the 'LVTH573 devices are transparent D-type latches. While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs.

A buffered output-enable  $(\overline{OE})$  input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

OE does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When  $V_{CC}$  is between 0 and 1.5 V, the devices are in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

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#### description (continued)

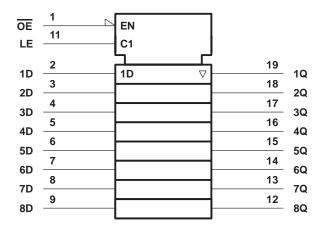
These devices are fully specified for hot-insertion applications using  $I_{off}$  and power-up 3-state. The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

The SN54LVTH573 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVTH573 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE (each latch)

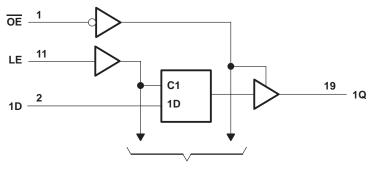
	OUTPUT		
OE	LE	D	Q
L	Н	Н	Н
L	Н	L	L
L	L	Χ	Q <sub>0</sub>
Н	X	Χ	Z

#### logic symbol†



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

#### logic diagram (positive logic)



To Seven Other Channels



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### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub>	
Input voltage range, V <sub>I</sub> (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high-impedance	
or power-off state, V <sub>O</sub> (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high state, V <sub>O</sub> (see Note 1)	
Current into any output in the low state, I <sub>O</sub> : SN54LVTH573	
SN74LVTH573	
Current into any output in the high state, IO (see Note 2): SN54LVTH573	48 mA
SN74LVTH573	64 mA
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	–50 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	
Package thermal impedance, θ <sub>JA</sub> (see Note 3): DB package	115°C/W
DW package	97°C/W
PW package	128°C/W
Storage temperature range, T <sub>stq</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

- 2. This current flows only when the output is in the high state and  $V_O > V_{CC}$ .
- 3. The package thermal impedance is calculated in accordance with JESD 51.

#### recommended operating conditions (see Note 4)

		SN54LV	TH573	SN74LV	UNIT		
			MIN	MAX	MIN	MAX	UNIT
Vcc	Supply voltage	2.7	3.6	2.7	3.6	V	
VIH	High-level input voltage	2		2		V	
V <sub>IL</sub>	Low-level input voltage		0.8		0.8	V	
VI	Input voltage		5.5		5.5	V	
ІОН	High-level output current		-24		-32	mA	
loL	Low-level output current					64	mA
Δt/Δν	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
Δt/ΔV <sub>CC</sub>	Power-up ramp rate		200		200		μs/V
T <sub>A</sub>	Operating free-air temperature	-55	125	-40	85	°C	

NOTE 4: All unused control inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

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### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			54LVTH	573	SN	UNIT					
PAR	AWEIER	TEST CO	CNDITIONS	MIN	TYP†	MAX	MIN	TYP†	MAX	UNIT			
VIK		$V_{CC} = 2.7 \text{ V}, \qquad I_{I} = -18 \text{ mA}$				-1.2			-1.2	V			
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V},$	I <sub>OH</sub> = -100 μA	V <sub>CC</sub> -0	.2		V <sub>CC</sub> -0	.2					
1/011		$V_{CC} = 2.7 \text{ V},$	$I_{OH} = -8 \text{ mA}$	2.4			2.4			V			
VOH		V <sub>CC</sub> = 3 V	I <sub>OH</sub> = -24 mA	2						v			
		VCC = 3 V	I <sub>OH</sub> = -32 mA				2						
		V <sub>CC</sub> = 2.7 V	I <sub>OL</sub> = 100 μA			0.2			0.2				
		VCC = 2.7 V	I <sub>OL</sub> = 24 mA			0.5			0.5				
VOL			I <sub>OL</sub> = 16 mA			0.4			0.4	V			
VOL		V <sub>CC</sub> = 3 V	I <sub>OL</sub> = 32 mA			0.5			0.5	v			
		VCC = 3 V	I <sub>OL</sub> = 48 mA	0.55									
			I <sub>OL</sub> = 64 mA						0.55	1			
		$V_{CC} = 0 \text{ or } 3.6 \text{ V},$	V <sub>I</sub> = 5.5 V			10	10						
١.	Control inputs	$V_{CC} = 3.6 \text{ V},$	$V_I = V_{CC}$ or GND		±1				±1				
11	Data inputs	V <sub>CC</sub> = 3.6 V	$V_I = V_{CC}$			1			1	μΑ			
	Data inputs		V <sub>I</sub> = 0			-5			<b>-</b> 5				
l <sub>off</sub>	$V_{CC} = 0,$ $V_{CC} = 0$		$V_I$ or $V_O = 0$ to 4.5 $V$						±100	μΑ			
		VCC = 3 V	V <sub>I</sub> = 0.8 V	75			75			μА			
II(hold)	Data inputs		V <sub>I</sub> = 2 V	-75			-75						
		$V_{CC} = 3.6 V^{\ddagger}$ ,	$V_{I} = 0 \text{ to } 3.6 \text{ V}$						±500				
lozh		$V_{CC} = 3.6 \text{ V},$	V <sub>O</sub> = 3 V			5			5	μΑ			
lozL		$V_{CC} = 3.6 \text{ V},$	$V_0 = 0.5 V$			<b>-</b> 5			<b>–</b> 5	μΑ			
I <sub>OZPU</sub>		$\frac{V_{CC}}{OE} = 0$ to 1.5 V, $V_{O} = 0$	0.5 V to 3 V,			±100*			±100	μА			
I <sub>OZPD</sub>	IOZPD $\frac{V_{CC} = 1.5 \text{ V to } 0, V_{O} = 0.5 \text{ V to } 3 \text{ V,}}{OE = \text{don't care}}$		0.5 V to 3 V,			±100*			±100	μА			
		V <sub>CC</sub> = 3.6 V,	Outputs high			0.19			0.19				
Icc	$I_{O} = 0$ ,	Outputs low	5		5		mA						
		$V_I = V_{CC}$ or GND	Outputs disabled			0.19			0.19				
		$V_{CC}$ = 3 V to 3.6 V, One input at $V_{CC}$ – 0.6 V, Other inputs at $V_{CC}$ or GND				0.2			0.2	mA			
Ci		V <sub>I</sub> = 3 V or 0			3			3		pF			
Co		V <sub>O</sub> = 3 V or 0			7			7		pF			

<sup>\*</sup>On products compliant to MIL-PRF-38535, this parameter is not production tested.

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

<sup>‡</sup> This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

<sup>§</sup> This is the increase in supply current for each input that is at the specified TTL voltage level rather than VCC or GND.

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## timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

			SN54L\	/TH573		SN74LVTH573				
			V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 2.7 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 2.7 V	
			MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>W</sub>	Pulse duration, LE high	3		3		3		3		ns
t <sub>su</sub>	Setup time, data before LE↓	0.7		0.6		0.7		0.6		ns
th	Hold time, data after LE↓	1.5		1.7		1.5		1.7		ns

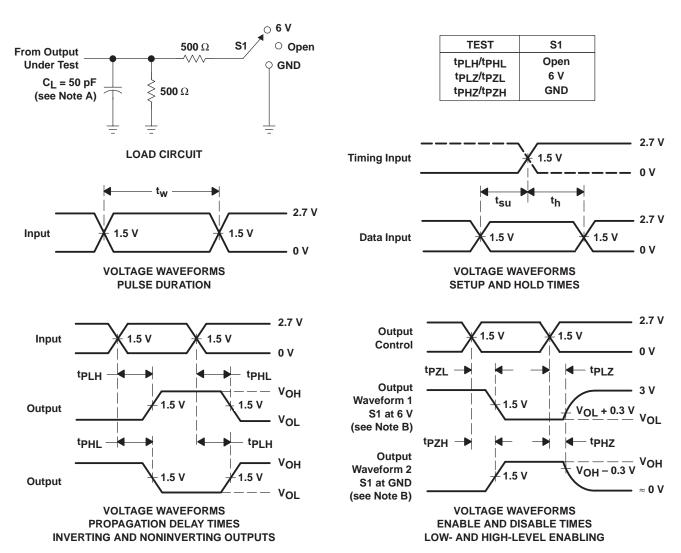
## switching characteristics over recommended free-air temperature, $C_L$ = 50 pF (unless otherwise noted) (see Figure 1)

			SN54LVTH573				SN74LVTH573					
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 3.3 V ± 0.3 V		V <sub>CC</sub> = 2.7 V		V <sub>CC</sub> = 3.3 V ± 0.3 V			V <sub>CC</sub> = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	MIN	TYP <sup>†</sup>	MAX	MIN	MAX	
t <sub>PLH</sub>	D	Q	1.4	4.1		4.7	1.5	2.6	3.9		4.5	ns
t <sub>PHL</sub>	Б	Q	1.4	4.5		4.8	1.5	2.9	3.9		4.5	115
t <sub>PLH</sub>	LE	Q	1	4.4		5.4	1.9	2.9	4.2		4.9	ns
<sup>t</sup> PHL		Q	1.4	4.4		5.1	1.9	2.9	4.2		4.9	115
<sup>t</sup> PZH	ŌĒ	Q	1.4	5.2		6.2	1.5	3.2	5.1		5.9	ns
tPZL		α	1.4	5.2		6.2	1.5	3.9	5.1		5.9	115
t <sub>PHZ</sub>	ŌĒ	Q	1.2	5.4		5.7	2	3.5	4.9		5.5	ns
tPLZ		OE	Q	1	5.2		5.2	2	3.2	4.6		4.9

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

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#### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50~\Omega$ ,  $t_f \leq$  2.5 ns,  $t_f \leq$  2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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